

Takayuki Iwasaki

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/631486/publications.pdf>

Version: 2024-02-01

59
papers

2,210
citations

304743

22
h-index

223800

46
g-index

59
all docs

59
docs citations

59
times ranked

2311
citing authors

#	ARTICLE	IF	CITATIONS
1	High growth rate synthesis of diamond film containing perfectly aligned nitrogen-vacancy centers by high-power density plasma CVD. <i>Diamond and Related Materials</i> , 2022, 123, 108840.	3.9	11
2	Coherence of a charge stabilised tin-vacancy spin in diamond. <i>Npj Quantum Information</i> , 2022, 8, .	6.7	16
3	Magnetic Field Generation System of the Magnetic Probe With Diamond Quantum Sensor and Ferromagnetic Materials for the Detection of Sentinel Lymph Nodes With Magnetic Nanoparticles. <i>IEEE Transactions on Magnetics</i> , 2021, 57, 1-5.	2.1	5
4	Thermometric quantum sensor using excited state of silicon vacancy centers in 4H-SiC devices. <i>Applied Physics Letters</i> , 2021, 118, .	3.3	12
5	Simultaneous thermometry and magnetometry using a fiber-coupled quantum diamond sensor. <i>Applied Physics Letters</i> , 2021, 118, .	3.3	26
6	Label-Free Phase Change Detection of Lipid Bilayers Using Nanoscale Diamond Magnetometry. <i>Advanced Quantum Technologies</i> , 2021, 4, 2000106.	3.9	7
7	Gradiometer Using Separated Diamond Quantum Magnetometers. <i>Sensors</i> , 2021, 21, 977.	3.8	8
8	Vector magnetometry using perfectly aligned nitrogen-vacancy center ensemble in diamond. <i>Applied Physics Letters</i> , 2021, 118, .	3.3	14
9	Photoelectrical detection of nitrogen-vacancy centers by utilizing diamond lateral p-n diodes. <i>Applied Physics Letters</i> , 2021, 118, .	3.3	9
10	Low-Temperature Spectroscopic Investigation of Lead-Vacancy Centers in Diamond Fabricated by High-Pressure and High-Temperature Treatment. <i>ACS Photonics</i> , 2021, 8, 2947-2954.	6.6	14
11	Spectroscopic investigations of negatively charged tin-vacancy centres in diamond. <i>New Journal of Physics</i> , 2020, 22, 013048.	2.9	62
12	Characterization of Schottky Barrier Diodes on Heteroepitaxial Diamond on 3C-SiC/Si Substrates. <i>IEEE Transactions on Electron Devices</i> , 2020, 67, 212-216.	3.0	11
13	Simultaneous wide-field imaging of phase and magnitude of AC magnetic signal using diamond quantum magnetometry. <i>Scientific Reports</i> , 2020, 10, 11611.	3.3	18
14	Vector Electrometry in a Wide-Gap-Semiconductor Device Using a Spin-Ensemble Quantum Sensor. <i>Physical Review Applied</i> , 2020, 14, .	3.8	17
15	Color centers based on heavy group-IV elements. <i>Semiconductors and Semimetals</i> , 2020, 103, 237-256.	0.7	5
16	Magnetometer with nitrogen-vacancy center in a bulk diamond for detecting magnetic nanoparticles in biomedical applications. <i>Scientific Reports</i> , 2020, 10, 2483.	3.3	66
17	A quantum thermometric sensing and analysis system using fluorescent nanodiamonds for the evaluation of living stem cell functions according to intracellular temperature. <i>Nanoscale Advances</i> , 2020, 2, 1859-1868.	4.6	37
18	Determination of Current Leakage Sites in Diamond p-n Junction. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2019, 216, 1900243.	1.8	1

#	ARTICLE	IF	CITATIONS
19	Effect of Si, Ge and Sn dopant elements on structure and photoluminescence of nano- and microdiamonds synthesized from organic compounds. <i>Diamond and Related Materials</i> , 2019, 93, 75-83.	3.9	38
20	Device engineering for diamond quantum sensors. , 2019, , .		1
21	Charge-state control of ensemble of nitrogen vacancy centers by n-diamond junctions. <i>Applied Physics Express</i> , 2018, 11, 033004.	2.4	10
22	Preferentially aligned nitrogen-vacancy centers in heteroepitaxial (111) diamonds on Si substrates via 3C-SiC intermediate layers. <i>Applied Physics Express</i> , 2018, 11, 045501.	2.4	12
23	Wide-field diamond magnetometry with millihertz frequency resolution and nanotesla sensitivity. <i>AIP Advances</i> , 2018, 8, .	1.3	13
24	Extending coherence time of macro-scale diamond magnetometer by dynamical decoupling with coplanar waveguide resonator. <i>Review of Scientific Instruments</i> , 2018, 89, 125007.	1.3	25
25	Thermal Stability of Perfectly Aligned Nitrogen-Vacancy Centers for High Sensitive Magnetometers. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2018, 215, 1800342.	1.8	13
26	In situ bias current monitoring of nucleation for epitaxial diamonds on 3C-SiC/Si substrates. <i>Diamond and Related Materials</i> , 2018, 88, 158-162.	3.9	13
27	Direct Nanoscale Sensing of the Internal Electric Field in Operating Semiconductor Devices Using Single Electron Spins. <i>ACS Nano</i> , 2017, 11, 1238-1245.	14.6	82
28	Highly oriented diamond (111) films synthesized by pulse bias-enhanced nucleation and epitaxial grain selection on a 3C-SiC/Si (111) substrate. <i>Applied Physics Letters</i> , 2017, 110, .	3.3	17
29	Influence of high-power density plasma on heteroepitaxial diamond nucleation on 3C-SiC surface. <i>Applied Physics Express</i> , 2017, 10, 045502.	2.4	9
30	Formation of perfectly aligned nitrogen-vacancy-center ensembles in chemical-vapor-deposition-grown diamond (111). <i>Applied Physics Express</i> , 2017, 10, 045501.	2.4	49
31	Observation of Interface Defects in Diamond Lateral p-n-Junction Diodes and Their Effect on Reverse Leakage Current. <i>IEEE Transactions on Electron Devices</i> , 2017, 64, 3298-3302.	3.0	6
32	High-Temperature Bipolar-Mode Operation of Normally-Off Diamond JFET. <i>IEEE Journal of the Electron Devices Society</i> , 2017, 5, 95-99.	2.1	27
33	Tin-Vacancy Quantum Emitters in Diamond. <i>Physical Review Letters</i> , 2017, 119, 253601.	7.8	204
34	Perfectly aligned shallow ensemble nitrogen-vacancy centers in (111) diamond. <i>Applied Physics Letters</i> , 2017, 111, .	3.3	45
35	Diamond electronics. , 2016, , .		2
36	Charge state modulation of nitrogen vacancy centers in diamond by applying a forward voltage across a p-n junction. <i>Diamond and Related Materials</i> , 2016, 63, 192-196.	3.9	18

#	ARTICLE	IF	CITATIONS
37	Normally-Off Diamond Junction Field-Effect Transistors With Submicrometer Channel. IEEE Electron Device Letters, 2016, 37, 209-211.	3.9	36
38	Quantifying selective alignment of ensemble nitrogen-vacancy centers in (111) diamond. Applied Physics Letters, 2015, 107, .	3.3	31
39	Heteroepitaxial growth of diamond films on 3C-SiC/Si substrates with utilization of antenna-edge microwave plasma CVD for nucleation. Japanese Journal of Applied Physics, 2015, 54, 04DH13.	1.5	17
40	Fabrication of diamond lateral p-n junction diodes on (111) substrates. Physica Status Solidi (A) Applications and Materials Science, 2015, 212, 2548-2552.	1.8	7
41	Germanium-Vacancy Single Color Centers in Diamond. Scientific Reports, 2015, 5, 12882.	3.3	251
42	Fluorinated Graphene FETs Controlled by Ionic Liquid Gate. Journal of Display Technology, 2014, 10, 962-965.	1.2	2
43	Polarization-controlled dressed-photon-phonon etching of patterned diamond structures. Physica Status Solidi (A) Applications and Materials Science, 2014, 211, 2339-2342.	1.8	7
44	600 V Diamond Junction Field-Effect Transistors Operated at 200 ^o C. IEEE Electron Device Letters, 2014, 35, 241-243.	3.9	74
45	Formation and structural analysis of twisted bilayer graphene on Ni(111) thin films. Surface Science, 2014, 625, 44-49.	1.9	18
46	Asymmetric transport property of fluorinated graphene. Applied Physics Letters, 2013, 103, 143106.	3.3	21
47	Improved visible light driven photoelectrochemical properties of 3C-SiC semiconductor with Pt nanoparticles for hydrogen generation. Applied Physics Letters, 2013, 103, .	3.3	20
48	Effect of radical fluorination on mono- and bi-layer graphene in Ar/F2 plasma. Applied Physics Letters, 2012, 101, .	3.3	45
49	Diamond Junction Field-Effect Transistors with Selectively Grown n ⁺ -Side Gates. Applied Physics Express, 2012, 5, 091301.	2.4	61
50	Electrical properties of lateral p-n junction diodes fabricated by selective growth of n ⁺ diamond. Physica Status Solidi (A) Applications and Materials Science, 2012, 209, 1761-1764.	1.8	32
51	Long-Range Ordered Single-Crystal Graphene on High-Quality Heteroepitaxial Ni Thin Films Grown on MgO(111). Nano Letters, 2011, 11, 79-84.	9.1	141
52	Al ₂ O ₃ / GeO _x / Ge gate stacks with low interface trap density fabricated by electron cyclotron resonance plasma postoxidation. Applied Physics Letters, 2011, 98, .	3.3	143
53	When is (D,C)-scaling both necessary and sufficient. IEEE Transactions on Automatic Control, 2000, 45, 1755-1759.	5.7	15
54	The dual iteration for fixed-order control. IEEE Transactions on Automatic Control, 1999, 44, 783-788.	5.7	124

#	ARTICLE	IF	CITATIONS
55	Well-posedness of feedback systems: insights into exact robustness analysis and approximate computations. IEEE Transactions on Automatic Control, 1998, 43, 619-630.	5.7	196
56	LPV system analysis with quadratic separator. , 0, , .		15
57	Integrated system design by separation. , 0, , .		23
58	LPV system analysis via quadratic separator for uncertain implicit systems. , 0, , .		7
59	Dynamical function design from a control perspective. , 0, , .		1